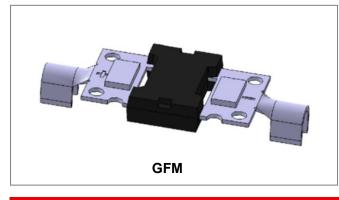


**GF3045TS** 

### Technical Data Data Sheet N2693, Rev.-

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# **GF3045TS Power Schottky Module Bypass Diode**



### **Mechanical Data**

- Case: GFM
- Terminals: Copper
- High temperature soldering guaranteed
- Heated-tool welding 260℃,10seconds
- Marking Code: GF3045TS

### Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm V <sub>rwm</sub> Vr	-	45	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=125°C, In DC	30	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	350	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.49	0.55	V
Reverse Current*	I <sub>R1</sub>	$@V_R = rated V_{R,} T_J = 25 \ ^{\circ}C$	0.02	0.2	mA
	I <sub>R2</sub>	$@V_R = rated V_{R,} T_J = 100 \ ^{\circ}C$	-	20	mA
Junction Capacitance	Ст	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	3680	_	pF

\* Pulse width < 300  $\mu s, \,$  duty cycle < 2%

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### Features

- Low thermal resistance
- Lower forward voltage drop, low power loss
- Isolate Package design, ideal for heat dispersion
- High forward current capability
- Trench MOS Schottky technology
- Excellent anti-humidity
- Low profile package
- High forward surge capability
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request



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### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	IN DC Forward Mode, without reverse bias, t $\leq$ 1 h	-55 to +200	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	-	1.5	°C/W

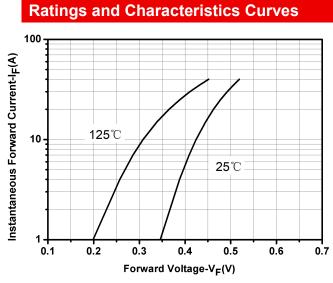


Fig.1-Typical Forward Voltage Characteristics

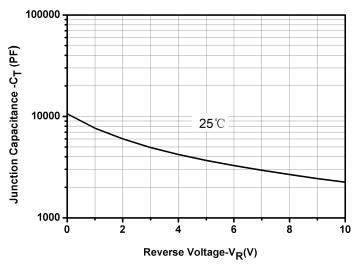


Fig.3-Capacitance vs. Reverse Voltage

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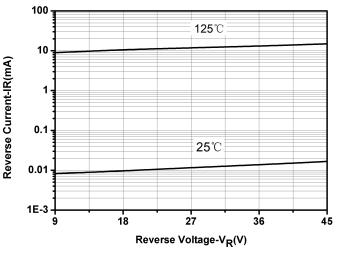


Fig.2-Typical Reverse Characteristics



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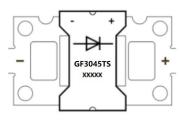
YY WW

L

### **Ordering Information**

Device	Package	Shipping
GF3045TS	GFM	30pcs / Tube

## **Marking Diagram**



Where XXXXX is YYWWL

- GF3045TS = Marking Code = Year
  - - = Week = Lot Number

Pb

Order P/N	Terminals	Additional	0	
GF3045TS-S1	Tin Plated	None	CF4050	Solder Paste
GF3045TS-S2	Tin Plated	Solder Paste □		
GF3045TS-S3	Tin Plated	Solder Block		
GF3045TS-N1	Nickel Plated	None		
GF3045TS-N2	Nickel Plated	Solder Paste		Solder Block
GF3045TS-N3	Nickel Plated	Solder Block		

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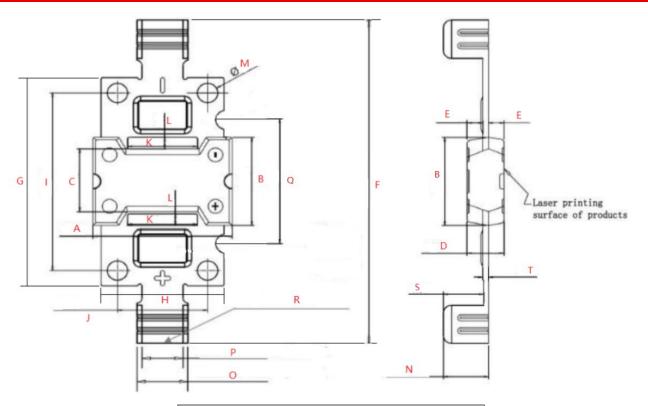


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### Mechanical Dimensions GFM (Millimeters)



Symbol	Dimensions in millimeters			
	Min.	Typical	Max	
A	16.90	17.00	17.10	
В	11.38	11.48	11.58	
C	8.15	8.20	8.25	
D	4.40	4.50	4.60	
E	1.85	1.90	1.95	
F	41.90	42.00	42.10	
G	26.90	27.00	27.10	
Н	14.90	15.00	15.60	
I	22.90	23.00	23.10	
J	10.90	11.00	11.10	
K	-	8.50	-	
L	-	1.50	-	
М	-	Ø 2.50	2.55	
N	5.35	5.50	5.65	
0	6.20	6.30	6.40	
Р	4.90	5.00	5.10	
Q	15.95	16.00	16.05	
R	2.80	2.90	3.00	
S	4.75	4.80	4.85	
Т	0.67	0.70	0.73	

Dimension H includes Burrs/cutting residuals.

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